Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2	(zinc near oxide) and (zinc near polar) and (oxygen near polar)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/06 08:34
L2	185	((zinc near oxide) or "ZnO") and (zinc or "Zn" near4 polar\$4) and (oxygen near4 polar)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/06 08:37
L3	11	((zinc near oxide) or "ZnO") and (zinc or "Zn" near4 polar\$4) and (oxygen near4 polar) and (light near emit\$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR .	ON	2007/06/06 08:38
L4	. 5	((zinc near oxide) or "ZnO") and (zinc or "Zn" near4 polar\$4) and (oxygen near4 polar) and (light near emit\$4) and sputter\$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/06 08:41
L5 .	26	((zinc near oxide) or "ZnO") and (zinc or "Zn" near4 polar\$4) and (oxygen near4 polar) and semiconductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/06 08:41
L6	10	((zinc near oxide) or "ZnO") and (zinc or "Zn" near4 polar\$4) and (oxygen near4 polar) and semiconductor and (LED or (light near emit\$4))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/06 08:42
L7	4	((zinc near oxide) or "ZnO") and (zinc or "Zn" near4 polar\$4) and (oxygen near4 polar) and semiconductor and (LED or (light near emit\$4)) and sputter\$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/06 08:49

L8	39	((zinc near oxide) or "ZnO") and (zinc or "Zn" near9 polar\$4) and (oxygen near9 polar\$4) and semiconductor and (LED or (light near emit\$4))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/06 09:01
L9	16040	((zinc near oxide) or "ZnO") near9 (semiconductor or wafer or substrate or carrier or base)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/06 09:03
L10	139	((zinc near oxide) or "ZnO") near9 (semiconductor or wafer or substrate or carrier or base) and ((zinc or ZnO) near9 polar\$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/06 09:03
L11	16	((zinc near oxide) or "ZnO") near9 (semiconductor or wafer or substrate or carrier or base) and ((zinc or ZnO) near9 polar\$4) and (oxygen near9 polar\$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR .	ON	2007/06/06 09:04
L12		((zinc near oxide) or "ZnO") near9 (semiconductor or wafer or substrate or carrier or base) and ((zinc or ZnO) near9 polar\$4) and (oxygen near9 polar\$4) and LED	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR .	ON	2007/06/06 09:07
L13		((zinc near oxide) or "ZnO") near9 (semiconductor or wafer or substrate or carrier or base) and ((zinc or ZnO) near9 polar\$4) and (oxygen near9 polar\$4) and (LED or (light near emit\$4))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/06 09:09
L14 ·	16	((zinc near oxide) or "ZnO") near9 (semiconductor or wafer or substrate or carrier or base) and ((zinc or ZnO) near9 polar\$4) and (oxygen near9 polar\$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/06 09:46

L15	763	((zinc near oxide) or "ZnO") near9 (semiconductor or wafer or substrate or carrier or base) and (multi near9 layer) and (LED or (light near emit\$4))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/06 09:47
L16	470	((zinc near oxide) or "ZnO") near9 (semiconductor or wafer or substrate or carrier or base) and (multi near9 layer) and (LED or (light near emit\$4)) and ("n-type" or (n near type)) and ("p-type" or (p near type))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/06 09:50
L17	13	((zinc near oxide) or "ZnO") near9 (semiconductor or wafer or substrate or carrier or base) and (multi near9 layer) and (LED or (light near emit\$4)) and ("n-type" or (n near type)) and ("p-type" or (p near type)) and contact and clad and (light near guide) and electrode	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR ·	ON	2007/06/06 09:51
L18	7	((zinc near oxide) or "ZnO") near9 (semiconductor or wafer or substrate or carrier or base) and (multi near9 layer) and (LED or (light near emit\$4)) and ("n-type" or (n near type)) and ("p-type" or (p near type)) and contact and clad and (light near guide) and electrode and (aluminum or nickel or gold)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/06 09:52
L19	2	((zinc near oxide) or "ZnO") near9 (semiconductor or wafer or substrate or carrier or base) and (multi near9 layer) and (LED or (light near emit\$4)) and ("n-type" or (n near type)) and ("p-type" or (p near type)) and contact and clad and (light near guide) and electrode and (aluminum or nickel or gold) and sputter\$4 and plasma and (MBE or MOCVD or LBE or laser)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/06 09:56
S1	1	(semiconductor or wafer or semiconductor) near4 (monocrystalline or crystal) and ("ZnO" and "zinc oxide") and (zinc near4 polar\$4) and (oxygen near polar) and (thin near4 film)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/13 08:42

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S2	1	(semiconductor or wafer or semiconductor) near4 (monocrystalline or crystal) and ("ZnO" and "zinc oxide") and (zinc near4 polar\$4) and (oxygen near polar)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/13 08:47
S3	93114	(semiconductor or wafer or semiconductor) near4 (monocrystalline or crystal or wurtzie)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/13 08:47
S4	2	(semiconductor or wafer or semiconductor) near4 (monocrystalline or crystal or wurtzie) and ("ZnO" or "zinc oxide") and (zinc near4 polar)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/13 10:31
S5	1	(semiconductor or wafer or semiconductor) near4 (monocrystalline or crystal or wurtzie) and ("ZnO" or "zinc oxide") and (zinc near4 polar) and (oxygen near4 polar)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/13 08:49
S6	4	(semiconductor or wafer or semiconductor) near8 (monocrystalline or crystal or wurtzie) and ("ZnO" or "zinc oxide") and (zinc near4 polar)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/13 10:32
S7	0	(semiconductor or wafer or semiconductor) near8 (monocrystalline or crystal) and wurtzie and ("ZnO" or "zinc oxide") and (zinc near4 polar)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/13 10:32
S8	0	(semiconductor or wafer or semiconductor) near8 (monocrystalline or crystal) and wurtzie	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/13 10:32
S9	0	wurtzie	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/13 10:34

S10	1817	wurtzite	US-PGPUB;	OR	ON	2006/07/13 10:34
			USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB		•	
S11	536	wurtzite near8 (semiconductor or wafer or substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/13 10:34
S12	202	wurtzite near8 ((semiconductor or wafer or substrate) near4 (monocrystalline or crystal))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/13 10:35
S13	98	wurtzite near8 ((semiconductor or wafer or substrate) near4 (monocrystalline or crystal)) and ("ZnO" or "zinc oxide")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/13 10:36
S14	0	wurtzite near8 ((semiconductor or wafer or substrate) near4 (monocrystalline or crystal)) and ("ZnO" or "zinc oxide") and (zinc near4 polar)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/13 10:36
S15	0	wurtzite near8 ((semiconductor or wafer or substrate) near4 (monocrystalline or crystal)) and ("ZnO" or "zinc oxide") and (oxygen near4 polar)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/13 10:37
S16	37	wurtzite near8 ((semiconductor or wafer or substrate) near4 (monocrystalline or crystal)) and ("ZnO" or "zinc oxide") and (thin near4 film)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/14 11:08
S17	6092	((semiconductor or wafer or substrate) near4 (monocrystalline or crystal)) and ("ZnO" or "zinc oxide") and (thin near4 film)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/13 10:47

S19	0	((semiconductor or wafer or substrate) near4 (monocrystalline or crystal)) and ("ZnO" or "zinc oxide") and (thin near4 film) and (zinc near4 polar) and (ox near4 polar)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR .	ON	2006/07/13 10:50
S20	2	((semiconductor or wafer or substrate) near4 (monocrystalline or crystal)) and ("ZnO" or "zinc oxide") and (thin near4 film) and (zinc near4 polar) and (oxygen near4 polar)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/13 10:50
S21	3	((semiconductor or wafer or substrate) near4 (monocrystalline or crystal)) and ("ZnO" or "zinc oxide") and (thin near4 film) and (zinc near4 polar) and (oxide near4 polar)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/13 10:50
S22	4	((semiconductor or wafer or substrate) near4 (monocrystalline or crystal)) and ("ZnO" or "zinc oxide") and (thin near4 film) and (zinc near4 polar)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/14 11:02
S23	236	("ZnO" or "zinc oxide") near8 wurtzite	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/14 11:08
S24	3	("ZnO" or "zinc oxide") near8 wurtzite and (zinc near4 polar)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/14 11:08
S25	3	("ZnO" or "zinc oxide") near8 wurtzite and (zinc near4 polar) and (oxygen near4 polar)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/14 11:09
S26	233196	crystal near8 (substrate or semiconductor or wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 13:40

S27	656	crystal near8 (substrate or semiconductor or wafer) and "zinc oxide" near4 (substrate or semiconductor or wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT;	OR .	OŅ	2006/08/04 13:41
S28	656	crystal near8 (substrate or semiconductor or wafer) and ("zinc oxide" near4 (substrate or semiconductor or wafer))	IBM_TDB US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 13:42
S29	3	crystal near8 (substrate or semiconductor or wafer) and ("zinc oxide" near4 (substrate or semiconductor or wafer)) and (zinc near4 polar)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 13:42
S30	1	crystal near8 (substrate or semiconductor or wafer) and ("zinc oxide" near4 (substrate or semiconductor or wafer)) and (zinc near4 polar) and (oxygen near4 polar)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 13:43
S31	26	crystal near8 (substrate or semiconductor or wafer) and ("zinc oxide" near4 (substrate or semiconductor or wafer)) and polar	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 13:43
S32	3	crystal near8 (substrate or semiconductor or wafer) and ("zinc oxide" near4 (substrate or semiconductor or wafer)) and polar and "LED"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 13:44
S33	12	crystal near8 (substrate or semiconductor or wafer) and ("zinc oxide" near4 (substrate or semiconductor or wafer)) and polar and (light near4 emit\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 13:44